



Progress of Optical Design for EUV Lithography Tools in BIT

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Introduction

Design of EUV projection objective

- Grouping design method
- Design of co-axial objective systems
- Design of off-axial objective systems

Design of EUV illuminator

- Reverse design/adjustment method
- Design results

Acknowledgment



Introduction



Constraints for illuminator

- pupil matching
- high uniformity at the arc-shaped field

Constraints for Objective

- High resolution
- > Almost none distortion
- Telecentricity on image side
- Accessible Stop
- Working distance
- > Low aspheric departure
- Small angle of incidence
- Chief ray angle at mask
- Total Tack



Trend of NA for projection objective





What is new in this year's presentation ?

I Design of co-axial objective systems

- 1. 6M objective with central obscuration (NA0.5)
- 2.8M unobscured objective (NA0.4)
- 3. 10M objective with central obscuration (NA0.75)

II Design of off-axial objective systems

6M unobscured objective (NA0.4)

III Design of EUV illuminator



Grouping Design for EUVL Objective

Parameter calculation condition

Non-Obstruction condition
Obscuration ratio condition
Pupil-stop condition
Conjugation condition

Grouping strategy (GS)

GS for 6-mirror objective
GS for 8-mirror objective
GS for 10-mirror objective

Spherical initial structure



Basic Group Database

- Object side group
- Image side group
- Obscured image side group
- •Middle two mirrors group
- •Middle four mirrors group



Basic Mirror Groups

Five Kinds of Mirror Groups





Grouping Strategy

6M unobscured objective :



G1: *M1*, *M*2 **G2**: *M*3, *M*4 **G3**: *M*5, *M*6

6M objective with central obscuration :

G1 : M1, M2 G2 : M3, M4 G3': M5, M6



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Grouping Strategy

8M unobscured objective



G1 : *M1, M2* G2' : *M3, M4, M5, M6* G3 : *M7, M8*

10M objective with central obscuration



Non-obstruction condition: The radius of one mirror can be expressed as a function of the clearance.

Clearance: The distance between the edge of a mirror and the beam near it.



- U_{ai} the slope angle of the upper marginal ray on M_i
- h_{ai} the ray height of the upper marginal ray on M_i
- h_{a0} the ray height of the ray beam near M_{i+1}

$$c_{i} = \sin\left(\frac{U_{ai}}{2} - \frac{\arctan\left(\left(h_{ai} - \left(h_{a0} - CL_{i}\right)\right) / \left(-d_{i}\right)\right)}{2}\right) / h_{ai}.$$

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Obscuration Ratio condition: The radius of one mirror can be expressed as a function of the ratio of hole to whole mirror diameter.



 $U_{\scriptstyle ai}$ the slope angle of upper marginal ray of $M_{\scriptstyle i}$

 h_{ai} height of upper marginal ray of M_i

 h_{aDi} height of upper marginal ray of the virtual surface D_i

 $radio_i$ the diameter ratio of the hole to the mirror M_i

$$c_{i} = \sin\left\{\frac{U_{ai}}{2} - \frac{\arctan\left[(h_{aDi+1}/radio_{i+1} - 2h_{aDi+1} + h_{ai})/(-d_{i})\right]}{2}\right\} / h_{ai}$$

Pupil-stop condition: Surface parameter is the function of the pupil or stop position .



 $h_{\rm zs}$ chief ray height on M_s

 $-d_s$ separation between M_s and M_{s+1}

 U_{zt} slope angle of the chief ray on M_s

 z_{zs} the along optical axial distance of the incident point on M_s

$$c_{s} = \sin(\frac{\arctan(h_{zs} / (-d_{s} + z_{zs}))}{2} - \frac{U_{zt}}{2}) / h_{zs}.$$

Conjugation condition: Surface parameters should match the adjacent groups' properties (e.g. petzval sum, object-image, Magification, pupil matching).



M denotes the magnification of the middle two mirror group

ps denotes the pezval sum of it

$$\begin{cases} d_{a-1} = l'_{a-1} - l_a = l'_{a-1} + Ml_{pa}l'_{pb} \left(-ps \cdot A \pm \sqrt{ps^2 A^2 - 4AB} \right) / A \\ c_a = -\frac{1}{2} \left(ps \pm \sqrt{ps^2 - 4B/A} \right) \\ d_a = A / \left(Ml'_{pb}l_{pa} \left(M^2 l_{pa} + 2Ml'_{pb}psl_{pa} - l'_{pb} \right) \right) \\ c_b = ps + c_a \\ d_b = l'_b - l_{b+1} = TT + l_a - d_a - l_{b+1} \end{cases}$$

$$ps^2 A^2 - 4AB > 0$$

$$\begin{cases} A = Ml'_{pb}l_{pa} \left(l_{pa}M^2TT + M^2l'_{pb}l_{pa} + 2Ml'_{pb}l_{pa} - l'_{pb}l_{pa} + l'_{pb}TT \right) \\ B = -ps^2 M^2 l_{pa}^2 l'_{pb}^2 - \frac{1}{2} M^2 l'_{pb}l_{pa} + \frac{1}{4} M^4 l_{pa}^2 + \frac{1}{4} l'_{pb}^2 \end{cases}$$

6M unobscured objective

-presented in 2013 EUVL work shop



1. 6M objective with central obscuration

To enable **11nm node**, 6-mirror with central obscuration is one of the

solutions. The NA of the objective is around 0.45.



- **G3'** is calculated under obscuration ratio condition firstly.
- G2 is then calculated under non-obstruction condition.
- To match the ray path of G2 and G3', G1 can be determined under conjugation condition.

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Performance



Ring field



Wavelength	avelength 13.5nm		
Numerical aperture	0.5		
A field of view	13mm×1mm		
Reduction	8		
Total track	1630mm		
working distance	34mm		
Chief ray angle on	<6.0°		
Chief ray angle on wafer	0.01°		
Wavefront error (RMS)	0.0285λ		
Distortion	<1.2nm		
Pupil obscuration	<25%		

Generation of new design forms



Other design forms

• **G3'** is fixed. Changing the separations of mirrors in **G2**, new design forms of **G2** will be obtained.

• To connect **G2** and **G3**, the design forms of **G1** will be changed accordingly.

•A new initial design are obtained by connecting the three groups.

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2.8M unobscured objective



NA	0.4
Reduction	4
TOTAL TRACK	947mm

NA	0.4
Reduction	4
TOTAL TRACK	1235mm



NA	0.4
Reduction	4
TOTAL TRACK	1274mm

3. 10M Objective with central obscuration

	(NA Reduction	0.7
			TOTAL TRACK	2743mm
NA	0.7			
Reduction	8			
TOTAL TRACK	2743mm			
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1. 6M objective off-axial unobscured system



Performance



Wavelength	13.5nm
Numerical aperture	0.4
A field of view	26mm×1.5mm
Reduction	4
Total track	1263mm
working distance	35mm
Chief ray angle on mask	<6.0°
Chief ray angle on wafer	0.18°
Wavefront error (RMS)	0.034λ
Distortion	1.8nm



Reverse design/ adjusting method for illuminator

Reverse design method:

- Object of the illuminator----exit pupil of objective
- Stop of the illuminator----arc shape field
- Design target: to match IF of given plasma source
- Para-position for pupil facets and field facets to ensure the illumination uniformity



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Reverse design/ adjusting method for illuminator

Reverse adjusting method:

➤A adjusting method for illuminator to match objectives with different NA and pupil parameters.

>Only the position of the component is adjusted. The figure of the component is the same.

ltem	Set 1	Set 2	Set 3
Wavelength	13.5nm		
Exposure field on the reticle	104mm 6mm, R=119mm		
Chief ray angle on the reticle	5.52 degree	6 degree	4.9 degree
demagnification	1/4	1/4	1/4
NA in image space	0.25	0.3	0.33

Reverse design method for illumination system



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Members of our EUV team





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Thanks for your attention!

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